

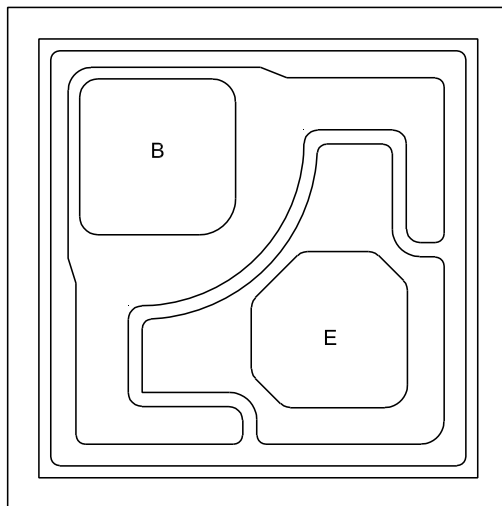
**PROCESS CP392V**  
**Small Signal Transistor**  
NPN - Amp/Switch Transistor Chip



**PROCESS DETAILS**

Process	EPITAXIAL PLANAR
Die Size	11 x 11 MILS
Die Thickness	7.1 MILS
Base Bonding Pad Area	3.7 x 3.7 MILS
Emitter Bonding Pad Area	3.7 x 3.7 MILS
Top Side Metalization	Al - 30,000Å
Back Side Metalization	Au - 12,000Å

**GEOMETRY**



BACKSIDE COLLECTOR

**GROSS DIE PER 4 INCH WAFER**

93,826

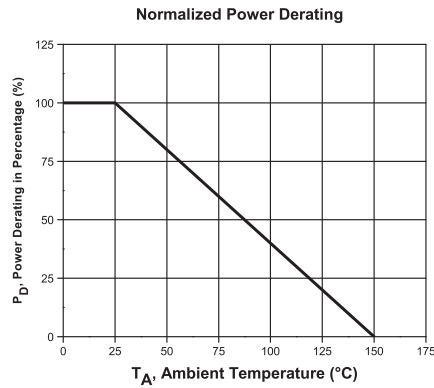
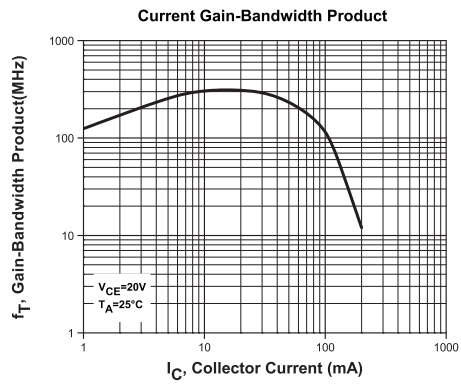
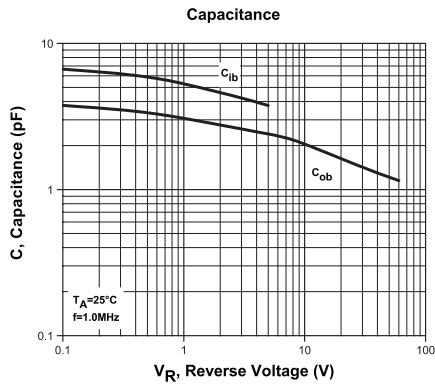
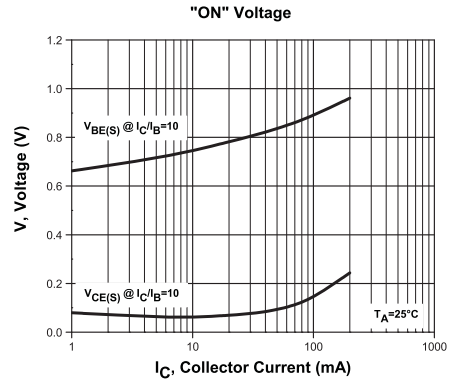
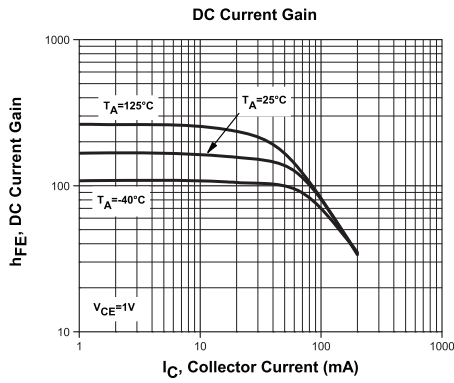
**PRINCIPAL DEVICE TYPES**

- 2N3904
- CMKT3904
- CMLT3904E
- CMPT3904
- CMPT3904E
- CMST3904
- CXT3904
- CZT3904

R2 (13-May 2010)

# PROCESS CP392V

## Typical Electrical Characteristics



R2 (13-May 2010)